

PN3645



PN3645



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 500 mA. Sourced from Process 63. See PN2907A for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CEO}	Collector-Emitter Voltage	60	V	
Vсво	Collector-Base Voltage	60	V	
V _{EBO}	Emitter-Base Voltage	5.0	V	
lc	Collector Current - Continuous	800	mA	
TJ, Tstg	Operating and Storage Junction Temperature Range	-55 to +150	°C	

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

Thermal Characteristics TA = 25°C unless otherwise noted				
Symbol	Characteristic	Max	Units	
		PN3645		
P _D	Total Device Dissipation	625	mW	
	Derate above 25°C	5.0	mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W	
$R_{\theta_{JA}}$	Thermal Resistance, Junction to Ambient	200	°C/W	

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PNP General Purpose Amplifier

(continued)

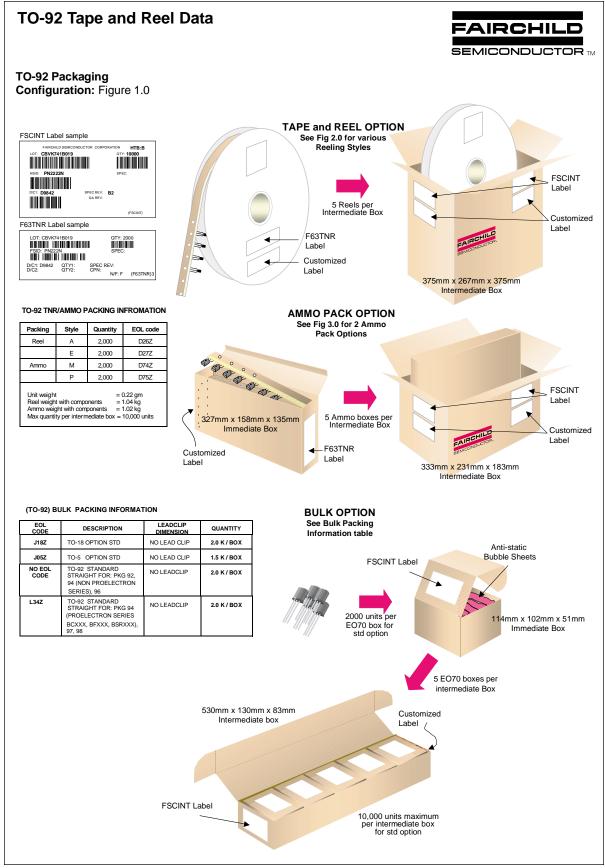
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10$ mA, $I_{\rm B} = 0$	60		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{E} = 10 \ \mu A, \ I_{C} = 0$	5.0		V
ICES	Collector-Cutoff Current	$V_{CB} = 50 \text{ V}, I_E = 0$ $V_{CB} = 50 \text{ V}, I_E = 0, T_A = 65 ^{\circ}\text{C}$		35 2.0	nA μA
I _{BL}	Base-Cutoff Current	$V_{CE} = 50 \text{ V}, \text{ I}_{C} = 0$		35	nA
	ACTERISTICS* DC Current Gain	V _{CE} = 10 V, I _C = 0.1 mA V _{CE} = 10 V, I _C = 1.0 mA	40 80		
			80 100 100 20	300	
h _{FE}		$ \begin{array}{l} V_{CE} = 10 \ V, \ I_C = 1.0 \ mA \\ V_{CE} = 10 \ V, \ I_C = 10 \ mA \\ V_{CE} = 10 \ V, \ I_C = 150 \ mA \\ V_{CE} = 2.0 \ V, \ I_C = 300 \ mA \\ V_{CE} = 1.0 \ V, \ I_C = 50 \ mA \\ \hline I_C = 50 \ mA, \ I_B = 2.5 \ mA \end{array} $	80 100 100	300 240 0.25 0.4	VVV
h _{FE} V _{CE(sat)}	DC Current Gain	$ \begin{array}{l} V_{CE} = 10 \ V, \ I_C = 1.0 \ mA \\ V_{CE} = 10 \ V, \ I_C = 10 \ mA \\ V_{CE} = 10 \ V, \ I_C = 150 \ mA \\ V_{CE} = 2.0 \ V, \ I_C = 300 \ mA \\ V_{CE} = 1.0 \ V, \ I_C = 50 \ mA \end{array} $	80 100 100 20	240 0.25	-
h _{FE} V _{CE(sat)} V _{BE(sat)}	DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage IGNAL CHARACTERISTICS	$\label{eq:VcE} \begin{array}{l} V_{CE} = 10 \ V, \ I_C = 1.0 \ mA \\ V_{CE} = 10 \ V, \ I_C = 10 \ mA \\ V_{CE} = 10 \ V, \ I_C = 150 \ mA \\ V_{CE} = 2.0 \ V, \ I_C = 300 \ mA \\ V_{CE} = 1.0 \ V, \ I_C = 50 \ mA \\ I_C = 50 \ mA, \ I_B = 2.5 \ mA \\ I_C = 150 \ mA, \ I_B = 15 \ mA \\ I_C = 150 \ mA, \ I_B = 15 \ mA \\ I_C = 150 \ mA, \ I_B = 15 \ mA \end{array}$	80 100 100 20	240 0.25 0.4 1.0 1.3	V V V
h _{FE} V _{CE(sat)} V _{BE(sat)} SMALL S	DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage IGNAL CHARACTERISTICS Output Capacitance	$\begin{split} V_{CE} &= 10 \ V, \ I_C = 1.0 \ mA \\ V_{CE} &= 10 \ V, \ I_C = 10 \ mA \\ V_{CE} &= 10 \ V, \ I_C = 150 \ mA \\ V_{CE} &= 2.0 \ V, \ I_C = 300 \ mA \\ V_{CE} &= 1.0 \ V, \ I_C = 50 \ mA \\ I_C &= 50 \ mA, \ I_B = 2.5 \ mA \\ I_C &= 150 \ mA, \ I_B = 15 \ mA \\ I_C &= 150 \ mA, \ I_B = 15 \ mA \\ I_C &= 150 \ mA, \ I_B = 15 \ mA \\ I_C &= 150 \ mA, \ I_B = 15 \ mA \\ I_C &= 150 \ mA, \ I_B = 15 \ mA \\ I_C &= 150 \ mA, \ I_B = 15 \ mA \\ I_C &= 150 \ mA, \ I_B = 15 \ mA \\ I_C &= 150 \ mA, \ I_B = 15 \ mA \\ I_C &= 150 \ mA, \ I_B = 15 \ mA \\ I_C &= 150 \ mA, \ I_B = 15 \ mA \\ I_C &= 150 \ mA, \ I_B = 15 \ mA \\ I_C &= 150 \ mA, \ I_B = 15 \ mA \\ I_C &= 150 \ mA, \ I_B = 15 \ mA \\ I_C &= 10 \ V, \ f = 140 \ kHz \\ \end{split}$	80 100 100 20	240 0.25 0.4 1.0	V
h _{FE} V _{CE(sat)} V _{BE(sat)}	DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage IGNAL CHARACTERISTICS	$\label{eq:VcE} \begin{array}{l} V_{CE} = 10 \ V, \ I_C = 1.0 \ mA \\ V_{CE} = 10 \ V, \ I_C = 10 \ mA \\ V_{CE} = 10 \ V, \ I_C = 150 \ mA \\ V_{CE} = 2.0 \ V, \ I_C = 300 \ mA \\ V_{CE} = 1.0 \ V, \ I_C = 50 \ mA \\ I_C = 50 \ mA, \ I_B = 2.5 \ mA \\ I_C = 150 \ mA, \ I_B = 15 \ mA \\ I_C = 150 \ mA, \ I_B = 15 \ mA \\ I_C = 150 \ mA, \ I_B = 15 \ mA \end{array}$	80 100 100 20	240 0.25 0.4 1.0 1.3	V V V

SWITCHING CHARACTERISTICS

ton	Turn-on Time	$V_{CC} = 30 \text{ V}, \text{ I}_{C} = 300 \text{ mA},$	40	ns
t _d	Delay Time	I _{B1} = 30 mA	25	ns
tr	Rise Time		35	ns
t _{off}	Turn-off Time	V _{CC} = 30 V, I _C = 300 mA	100	ns
ts	Storage Time	I _{B1} = I _{B2} = 30 mA	70	ns
t _f	Fall Time		50	ns

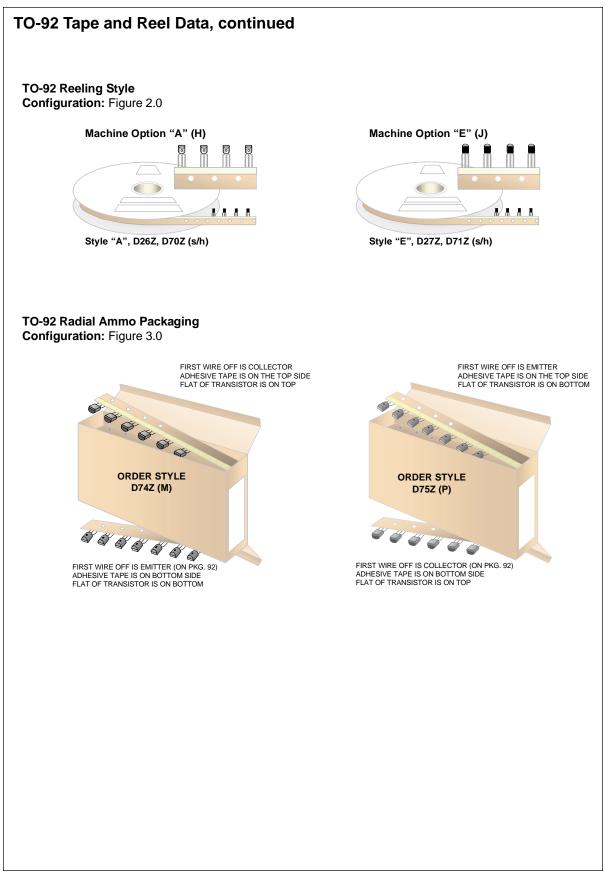
*Pulse Test: Pulse Width $\leq 300~\mu\text{s},~\text{Duty}~\text{Cycle} \leq 2.0\%$

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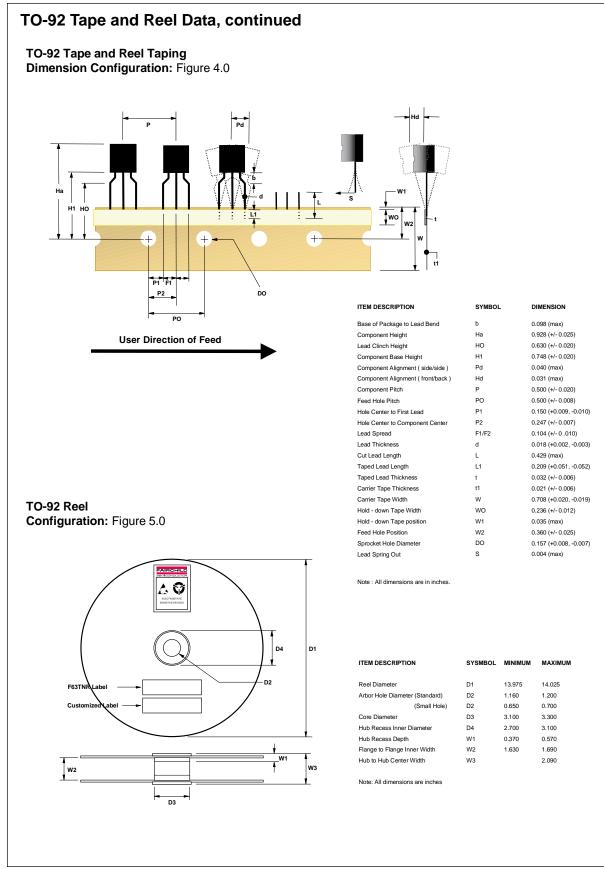


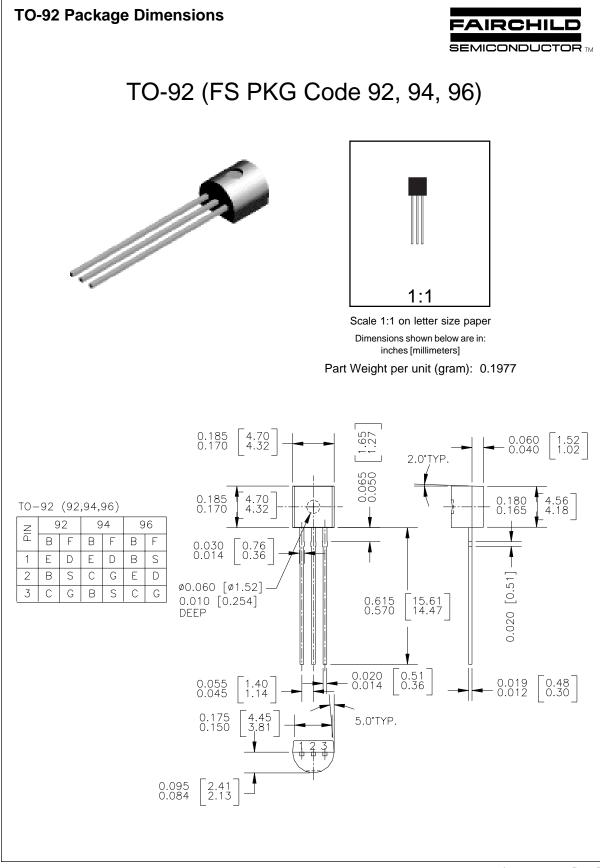
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